

MANUFACTURING METHOD OF CHIPS

ABSTRACT

First penetrating paths that penetrate an insulating film are formed by irradiation with a laser beam along the boundaries of multiple devices from a surface side of the insulating film prior to formation of a mask used when a wafer is divided by plasma etching (protective film forming step and second laser beam irradiation step). In this case, the irradiation condition of the laser beam for removing the desired part of the insulating film and the irradiation condition of the laser beam for forming the mask, that is, for removing the desired part of a protective film, can each be set to a preferable condition. As a result, it becomes possible to improve the processing accuracy when the wafer is divided to manufacture chips.

[FIG. 2]